

< C band internally matched power GaAs FET >

MGFC39V7785A

7.7 - 8.5 GHz BAND / 8W

DESCRIPTION

The MGFC39V7785A is an internally impedance-matched GaAs power FET especially designed for use in 7.7 – 8.5 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

• High output power

P1dB=8W (TYP.) @f=7.7 - 8.5GHz

• High power gain

GLP= 7.5dB (TYP.) @f=7.7 - 8.5GHz

High power added efficiency

P.A.E.=27% (TYP.) @f=7.7 - 8.5GHz

• Low distortion [item -51]

IM3=-45dBc (TYP.) @Po=28dBm S.C.L

APPLICATION

• item 01: 7.7 – 8.5 GHz band power amplifier

• item 51: 7.7 – 8.5 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=2.4A Refer to Bias Procedure • RG=50ohm

Absolute maximum ratings (Ta=25°C)

| V |
|----|
| |
| V |
| Α |
| mA |
| mA |
| W |
| °C |
| °C |
| _ |

1 : Tc=25°C

OUTLINE DRAWING Unit: millimeters 21.0 +/-0.3 12.9 +/-0.2 (3)

Keep Safety first in your circuit designs! Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (I) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Electrical characteristics (Ta=25°C)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|--------------|--------------------------------------|-------------------------|--------|------|------|------|
| | | | Min. | Тур. | Max. | |
| IDSS | Saturated drain current | VDS=3V,VGS=0V | - | - | 7.5 | Α |
| gm | Transconductance | VDS=3V,ID=2.2A | - | 2 | - | S |
| VGS(off) | Gate to source cut-off voltage | VDS=3V,ID=20mA | - | - | -4.5 | V |
| P1dB | Output power at 1dB gain compression | VDS=10V,ID(RF off)=2.4A | 38 | 39.5 | - | dBm |
| GLP | Linear Power Gain | f=7.7 – 8.5GHz | 6 | 7.5 | - | dB |
| ID | Drain current | | - | - | 3 | Α |
| P.A.E. | Power added efficiency | | - | 27 | - | % |
| IM3 *2 | 3rd order IM distortion | | -42 | -45 | - | dBc |
| Rth(ch-c) *3 | Thermal resistance | delta Vf method | - | - | 3.5 | °C/W |

^{*2 :}item -51 ,2 tone test,Po=28dBm Single Carrier Level ,f=8.5GHz,delta f=10MHz

^{*3:} Channel-case

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